L Number	Hits	Search Text	DB	Time stamp
-	9503	trench with nitride	USPAT;	2004/08/04 09:50
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	2420	I state that the marks	IBM_TDB	2004/00/02 12:51
-	2128	hemispherical with grain	USPAT;	2004/08/03 12:51
			US-PGPUB; EPO; JPO;	-
			DERWENT;	
			IBM_TDB	
-	103	(trench with nitride) and (hemispherical with grain)	USPAT;	2004/08/03 12:51
		, , , , , , , , , , , , , , , , , , , ,	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	:
			IBM_TDB	0004/00/00 40 54
<del>-</del>	547	etch\$3 with HSG	USPAT;	2004/08/03 12:51
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	86	438/FOR.100.ccls.	USPAT;	2004/08/03 12:51
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0004/00/00 40 54
-	587	438/243.ccls.	USPAT;	2004/08/03 12:51
	146	438/246.ccls.	US-PGPUB USPAT;	2004/08/03 12:51
-	140	436/240.CCIS.	US-PGPUB	2004/00/03 12.31
_	111	438/249.ccls.	USPAT;	2004/08/03 12:51
			US-PGPUB	
-	510	438/386.ccls.	USPAT;	2004/08/03 12:51
			US-PGPUB	
-	91	438/389.ccls.	USPAT;	2004/08/03 12:51
	600	420/255	US-PGPUB	2004/00/02 12:51
-	680	438/255.ccls.	USPAT; US-PGPUB	2004/08/03 12:51
_	727	438/398.ccls.	USPAT;	2004/08/03 12:51
	727	130/330.003.	US-PGPUB	200 1,00,00 12.01
-	261	438/964.ccls.	USPAT;	2004/08/03 12:51
			US-PGPUB	
-	61	438/FOR.220.ccls.	USPAT;	2004/08/03 12:51
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	262	438/558.ccls.	USPAT;	2004/08/03 12:51
			US-PGPUB	, = -, = = =====
-	1482515	plate electrode	USPAT;	2004/08/03 12:51
			US-PGPUB	
-	245	438/563.ccls.	USPAT;	2004/08/03 12:51
	216262	diffusion diffust?	US-PGPUB USPAT;	2004/09/03 12:51
-	316262	diffusion diffus\$3	US-PGPUB	2004/08/03 12:51
-	1075566	glass oxide	USPAT;	2004/08/03 12:51
		<u> </u>	US-PGPUB	, 15, 15
-	273051	capacitor	USPAT;	2004/08/03 12:51
			US-PGPUB	
	474414	trench recess	USPAT;	2004/08/03 12:51
	2422	has	US-PGPUB	2004/00/02 42 51
•	2103	hsg	USPAT; US-PGPUB	2004/08/03 12:51
	<u> </u>		1 03-FGFUD	l

-	7297	(plate electrode) with (diffusion diffus\$3) with (glass oxide)	USPAT; US-PGPUB	2004/08/03 12:51
-	71	((trench with nitride) and (hemispherical with grain) and capacitor) not ((trench with nitride) same (hemispherical with	USPAT; US-PGPUB;	2004/08/03 12:51
		grain))	EPO; JPO; DERWENT; IBM_TDB	
-	18	(trench with nitride) same (hemispherical with grain)	USPAT; US-PGPUB;	2004/08/03 12:51
	:		EPO; JPO; DERWENT; IBM_TDB	
-	85	((trench with nitride) and (hemispherical with grain)) not ((trench with nitride) same (hemispherical with grain))	USPAT; US-PGPUB;	2004/08/03 12:51
			EPO; JPO; DERWENT;	
-	509	(etch\$3 with HSG) and (capacitor node plate)	IBM_TDB USPAT; US-PGPUB;	2004/08/03 12:51
			EPO; JPO; DERWENT;	
-	39	148/DIG.138.ccls.	IBM_TDB USPAT; US-PGPUB;	2004/08/03 12:51
			EPO; JPO; DERWENT;	
-	54	438/FOR.488.ccls.	IBM_TDB USPAT; US-PGPUB;	2004/08/03 12:51
			EPO; JPO; DERWENT;	
-	85	438/392.ccls.	IBM_TDB USPAT; US-PGPUB	2004/08/03 12:51
-	116	438/923.ccls.	USPAT; US-PGPUB	2004/08/03 12:51
-	35	((plate electrode) with (diffusion diffus\$3) with (glass oxide)) and capacitor and (trench recess) and hsg	USPAT; US-PGPUB	2004/08/03 12:51
-	87	(trench with nitride) and (hemispherical with grain) and capacitor	USPAT; US-PGPUB; EPO; JPO;	2004/08/03 12:57
			DERWENT; IBM_TDB	
-	83	((trench with nitride) and (hemispherical with grain) and capacitor) not (@ad>20030423 @rlad>20030423)	USPAT; US-PGPUB; EPO; JPO;	2004/08/03 12:58
			DERWENT; IBM_TDB	
-	3387	"doped oxide"	USPAT; US-PGPUB; EPO; JPO;	2004/08/04 09:50
			DERWENT; IBM_TDB	
-	0	(NH4OH with etchant) same "doped oxide"	USPAT; US-PGPUB; EPO; JPO;	2004/08/04 09:51
			DERWENT; IBM_TDB	
-	0	(NH4OH with etchant) and "doped oxide"	USPAT; US-PGPUB; EPO; JPO;	2004/08/04 09:51
			DERWENT; IBM_TDB	

	T			
-	5	(NH4OH with etchant) same oxide	USPAT;	2004/08/04 09:51
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	62	NH4OH with etchant	USPAT;	2004/08/04 09:58
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	370685	@ad>20030423 @rlad>20030423	USPAT;	2004/08/04 09:59
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	60	(NH4OH with etchant) not (@ad>20030423 @rlad>20030423)	USPAT;	2004/08/04 13:56
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	6306724.pn.	USPAT	2004/08/04 14:02
-	1	5911109.pn.	USPAT	2004/08/04 15:39
_	1	6242323.pn.	USPAT	2004/08/04 15:55
1 -	173	recess with "pad oxide"	USPAT;	2004/08/04 15:56
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	9	(recess with "pad oxide") same capacitor	USPAT;	2004/08/04 15:56
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	1.		IBM_TDB	